

HAT2179R

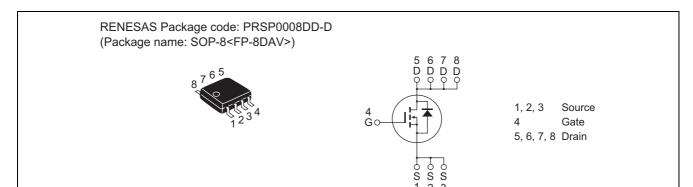
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1570-0100 Rev.1.00 Jul 06, 2007

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

ltem	Symbol	Ratings	Unit	
Drain to source voltage	V_{DSS}	600	V	
Gate to source voltage	V_{GSS}	±30	V	
Drain current	I _D	0.7	А	
Drain peak current	I _{D (pulse)} Note1	2.0	А	
Body-drain diode reverse drain current	I _{DR}	0.7	А	
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	2.0	А	
Channel dissipation	Pch Note2	2.5	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. $PW \le 10 \mu s$, duty cycle $\le 1\%$

2. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10 s

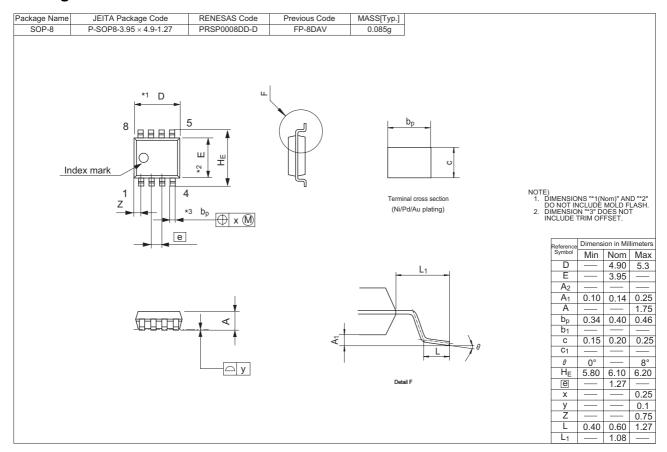
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	5.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	yfs	0.8	1.2	_	S	$I_D = 0.4 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state resistance	R _{DS(on)}	_	3.5	4.5	Ω	$I_D = 0.4 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	280	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	31	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	3.8	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	24	_	ns	I _D = 0.4 A
Rise time	t _r	_	15	_	ns	V _{GS} = 10 V
Turn-off delay time	$t_{d(off)}$	_	50	_	ns	$R_L = 750 \Omega$
Fall time	t _f	_	58	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	10	_	nC	V _{DD} = 480 V
Gate to source charge	Qgs	_	1.6	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd	_	5.4	_	nC	$I_D = 0.7 A$
Body-drain diode forward voltage	V_{DF}	_	0.8	1.2	V	$I_F = 0.7 \text{ A}, V_{GS} = 0^{\text{Note3}}$
Body-drain diode reverse recovery time	t _{rr}	_	200	_	ns	$I_F = 0.7 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 3. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2179R-EL-E	2500 pcs	Taping

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